50V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
50V	15mΩ @ V_{GS} = 10V	9.1A
	23mΩ @ V_{GS} = 4.5V	7.4A

Features

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm^2
- Low Gate Threshold Voltage
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

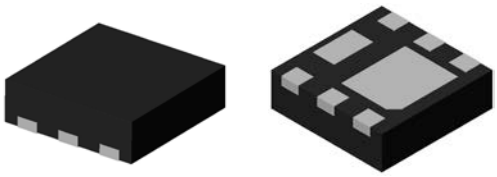
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load Switch
- Adaptor Switch
- Notebook PC

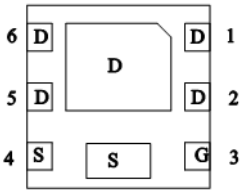
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.007 grams (Approximate)

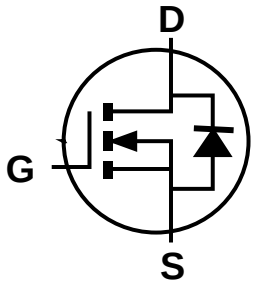
U-DFN2020-6



Top View Bottom View



Pin Out
Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per reel
DMT5015LFDF-7	T5	7	3,000
DMT5015LFDF-13	T5	13	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

T5 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2014)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	50	V
Gate-Source Voltage			V_{GSS}	±16	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	9.1 7.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	11.5 9.2	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	60	A
Continuous Source-Drain Diode Current		T_A = +25°C	I_S	2.2	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	14.4	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	10.4	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.82	W
	T_A = +70°C		0.52	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	153	°C/W
	t<10s		96	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.97	W
	T_A = +70°C		1.2	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	67	°C/W
	t<10s		42	
Thermal Resistance, Junction to Case (Note 6)	Steady state	$R_{\theta JC}$	14	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	—	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	15	mΩ	V_{GS} = 10V, I_D = 8A
			—	23		V_{GS} = 4.5V, I_D = 6A
Diode Forward Voltage	V_{SD}	—	0.7	1.0	V	V_{GS} = 0V, I_S = 5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	902.7	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	301.4	—		
Reverse Transfer Capacitance	C_{rss}	—	15.2	—		
Gate Resistance	R_g	—	1.9	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6.1	—	nC	V_{DS} = 25V, I_D = 8A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	14	—		
Gate-Source Charge	Q_{gs}	—	2.4	—		
Gate-Drain Charge	Q_{gd}	—	1.6	—		
Turn-On Delay Time	$t_{D(on)}$	—	2.8	—	ns	V_{DS} = 25V, V_{GS} = 10V, R_G = 3Ω, I_D = 8A
Turn-On Rise Time	t_r	—	5.1	—		
Turn-Off Delay Time	$t_{D(off)}$	—	10.6	—		
Turn-Off Fall Time	t_f	—	2.7	—		
Reverse Recovery Time	t_{rr}	—	18.9	—	ns	I_F = 8A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{rr}	—-	9.2	—	nC	I_F = 8A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

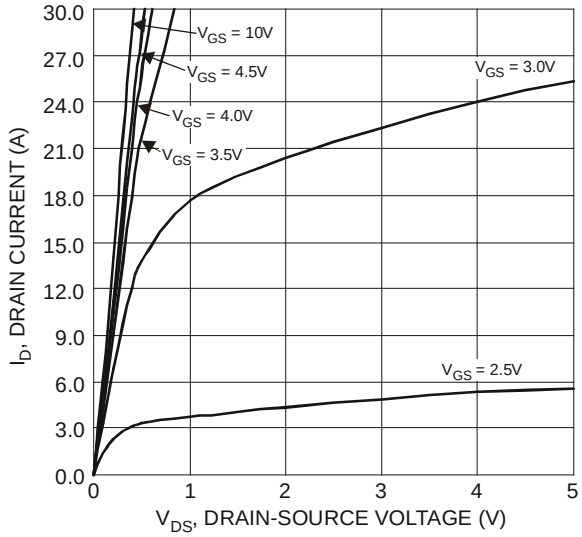


Figure 1 Typical Output Characteristics

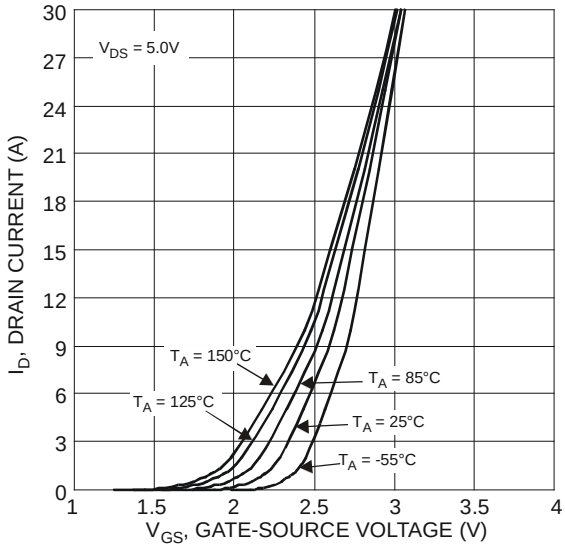


Figure 2 Typical Transfer Characteristics

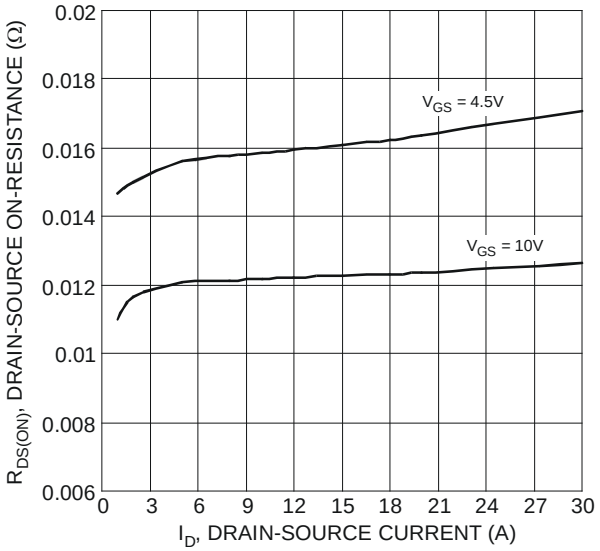


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

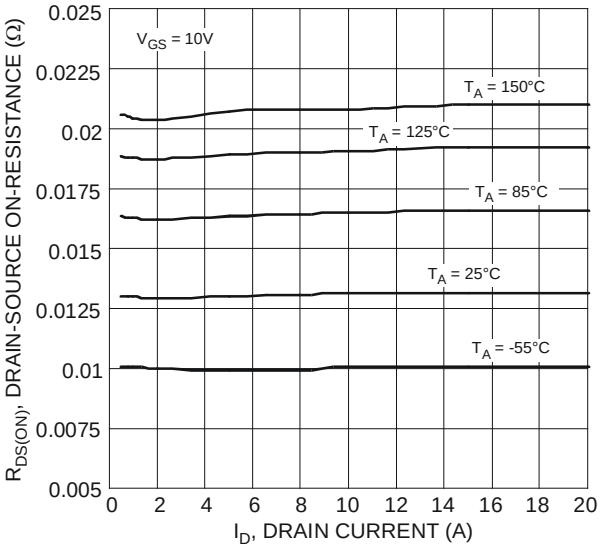


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

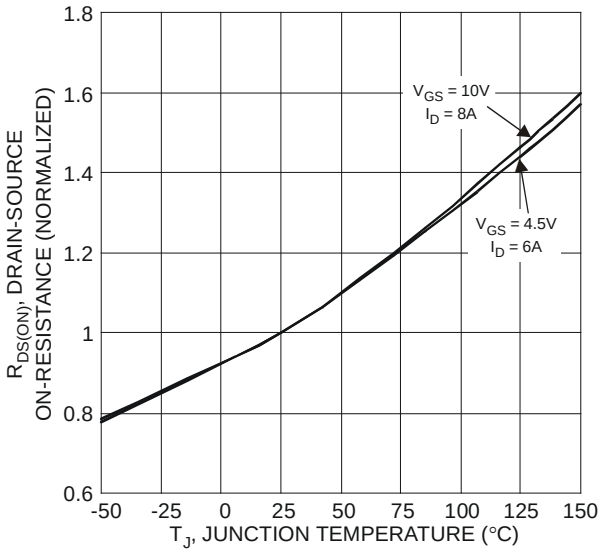


Figure 5 On-Resistance Variation with Temperature

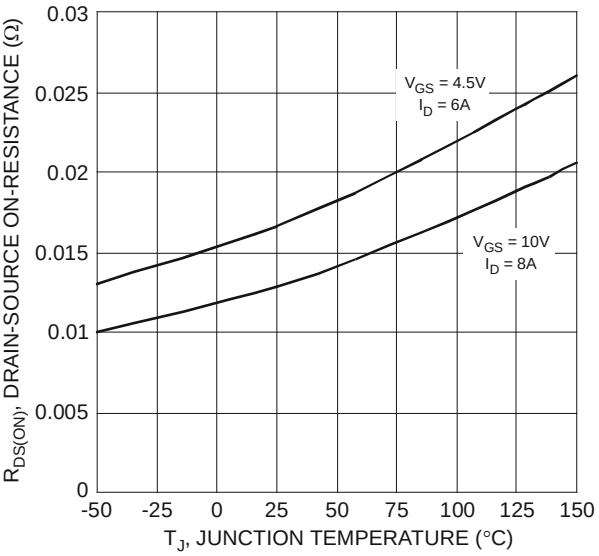


Figure 6 On-Resistance Variation with Temperature

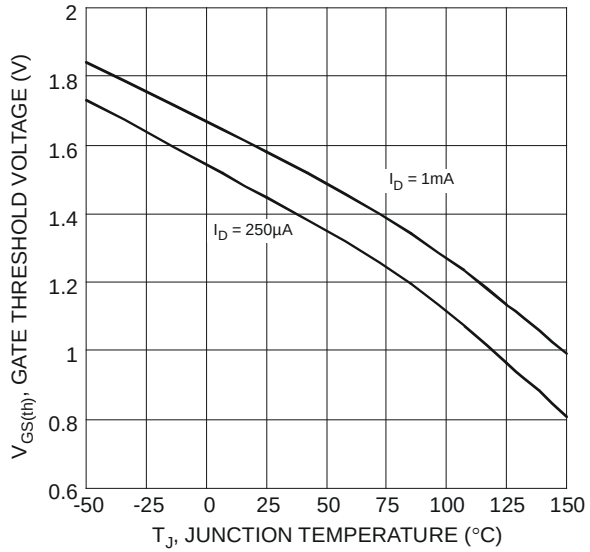


Figure 7 Gate Threshold Variation vs. Ambient Temperature

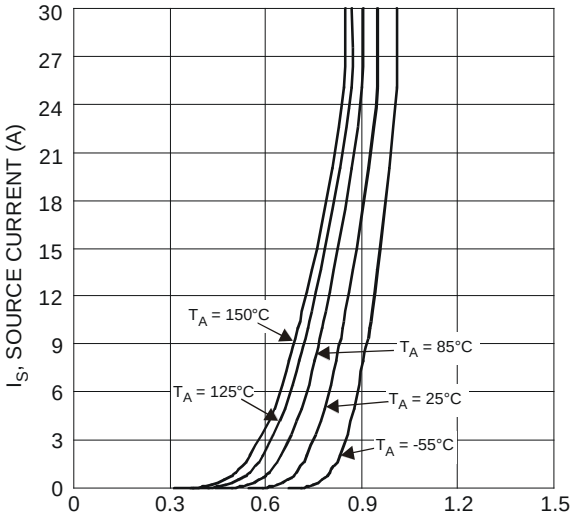


Figure 8 Diode Forward Voltage vs. Current

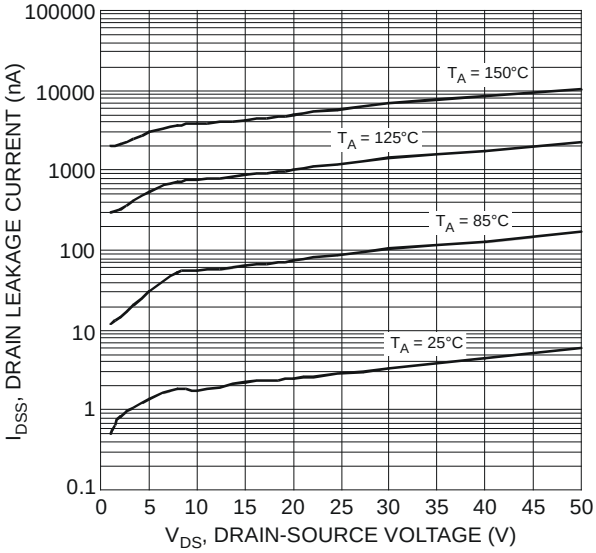


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

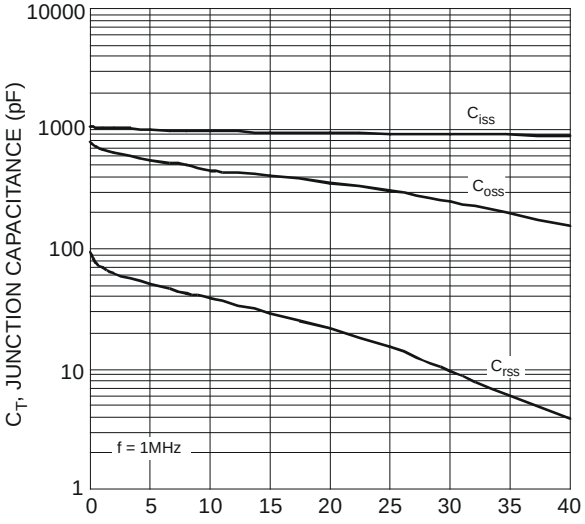


Figure 10 Typical Junction Capacitance

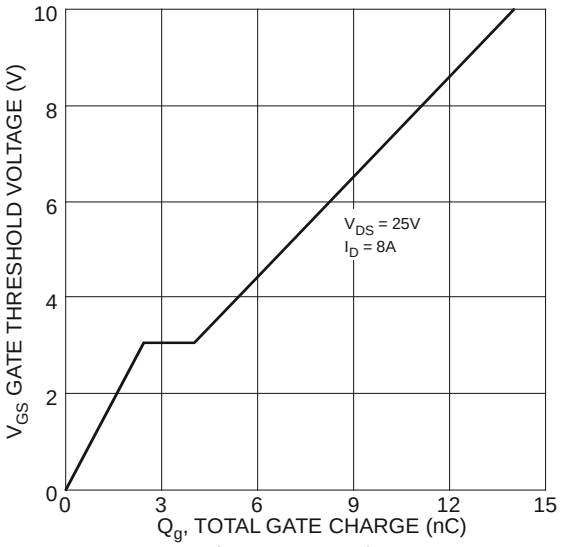


Figure 11 Gate Charge

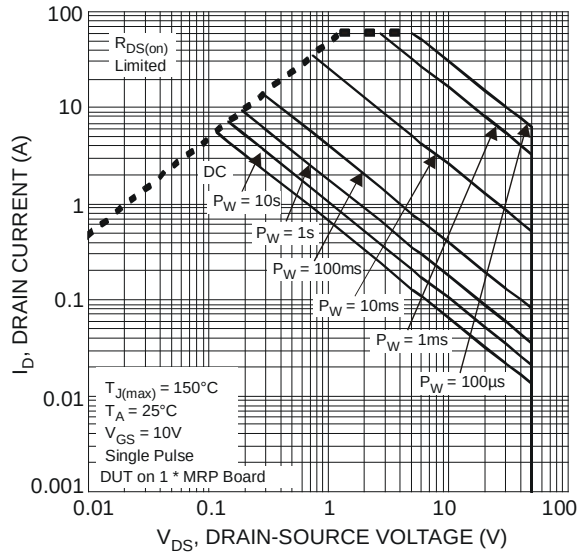


Figure 12 SOA, Safe Operation Area

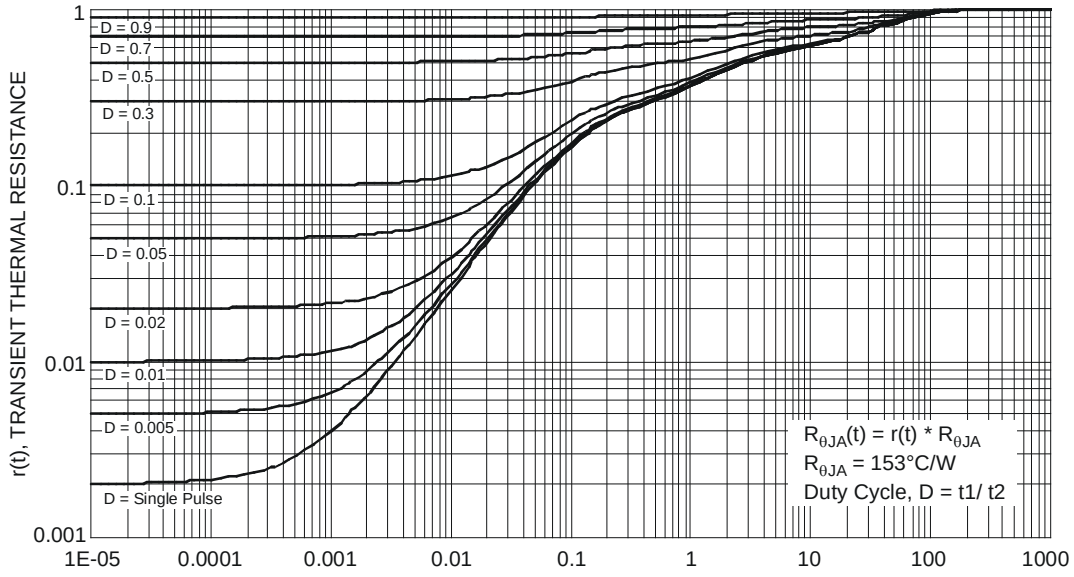
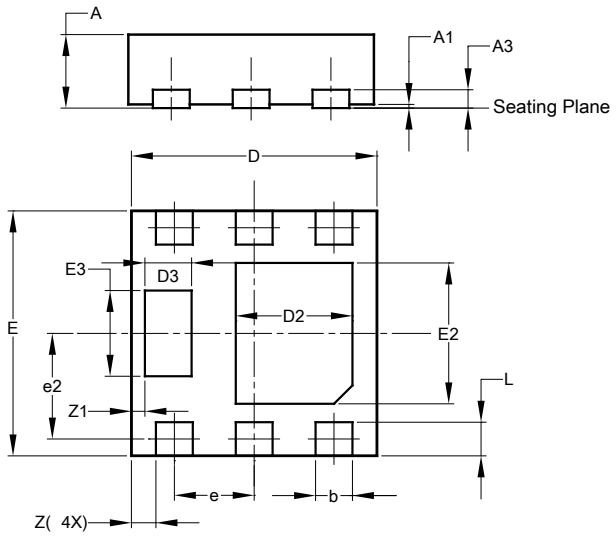


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

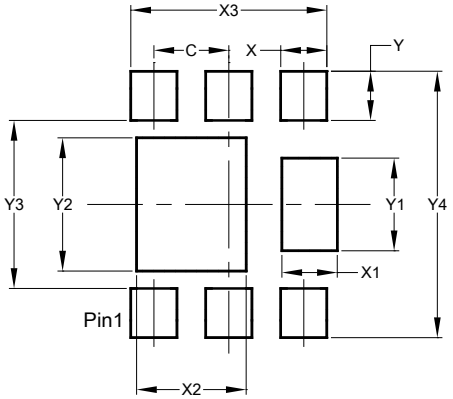
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-DFN2020-6 (Type F)			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D3	0.33	0.43	0.38
e	0.65 BSC		
e2	0.863 BSC		
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E3	0.65	0.75	0.70
L	0.225	0.325	0.275
Z	0.20 BSC		
Z1	0.110 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



U-DFN2020-6 (Type F)

Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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